

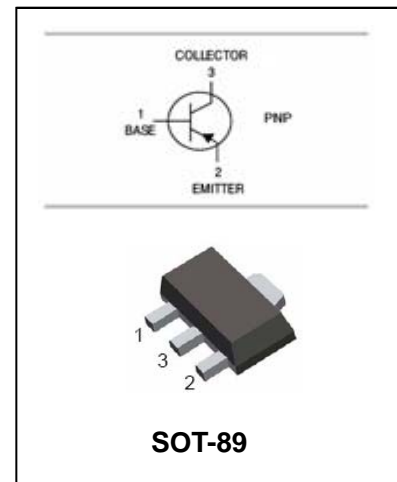


Silicon Planar Epitaxial Transistor

2SA1204

FEATURES

- Suitable for output stage of 3 watts Amplifier
- Suitable flat package
- High DC current gain
- $P_C=1.0$ to $2.0W$ (mounted on ceramic substrate)
- Complementary to 2SC2884



ORDERING INFORMATION

Type No.	Marking	Package Code
2SA1204	RO/RV	SOT-89

MAXIMUM RATING @ $T_a=25^{\circ}C$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-35	V
V_{CEO}	Collector-Emitter Voltage	-35	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-800	mA
I_B	Base Current	-160	mA
P_C	Collector Dissipation	500 1000(Note)	mW
T_j, T_{stg}	Junction and Storage Temperature	-55~150	$^{\circ}C$

Note1: Mounted on ceramic substrate($250mm^2 \times 0.8t$)

**Silicon Planar Epitaxial Transistor****2SA1204****ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-30			V
Collector cut-off current	I_{CBO}	$V_{CB}=-35V, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-1V, I_C=-100mA$	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500mA, I_B=-20mA$			-0.7	V
Base-emitter	V_{BE}	$V_{CE}=-1V, I_C=-10mA$	-0.5		-0.8	V
Transition frequency	f_T	$V_{CE}=-5V, I_C=-10mA$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$		19		pF

CLASSIFICATION OF h_{FE}

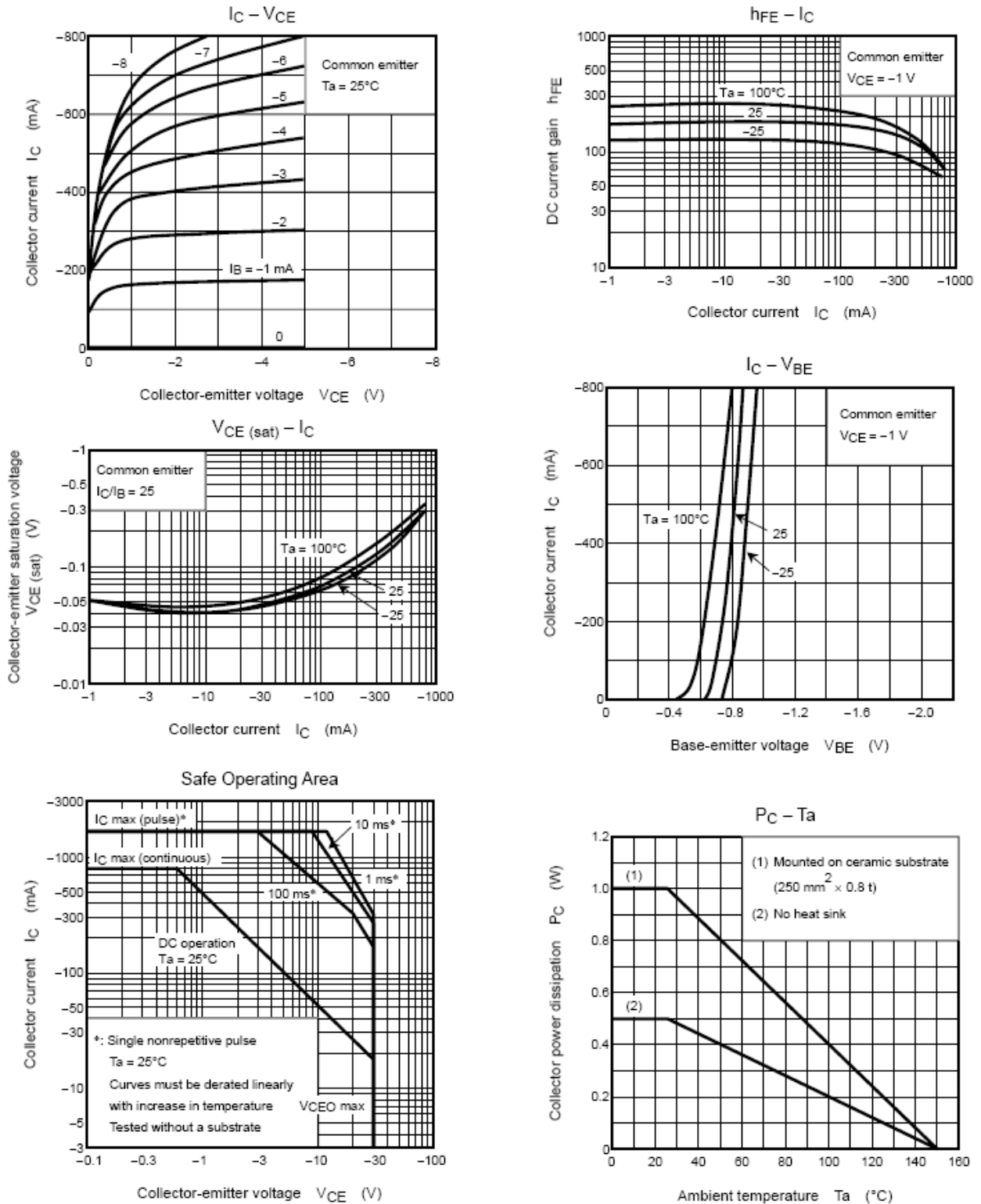
Rank	O	Y
Range	100-200	160-320
Marking	RO	RY



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TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified



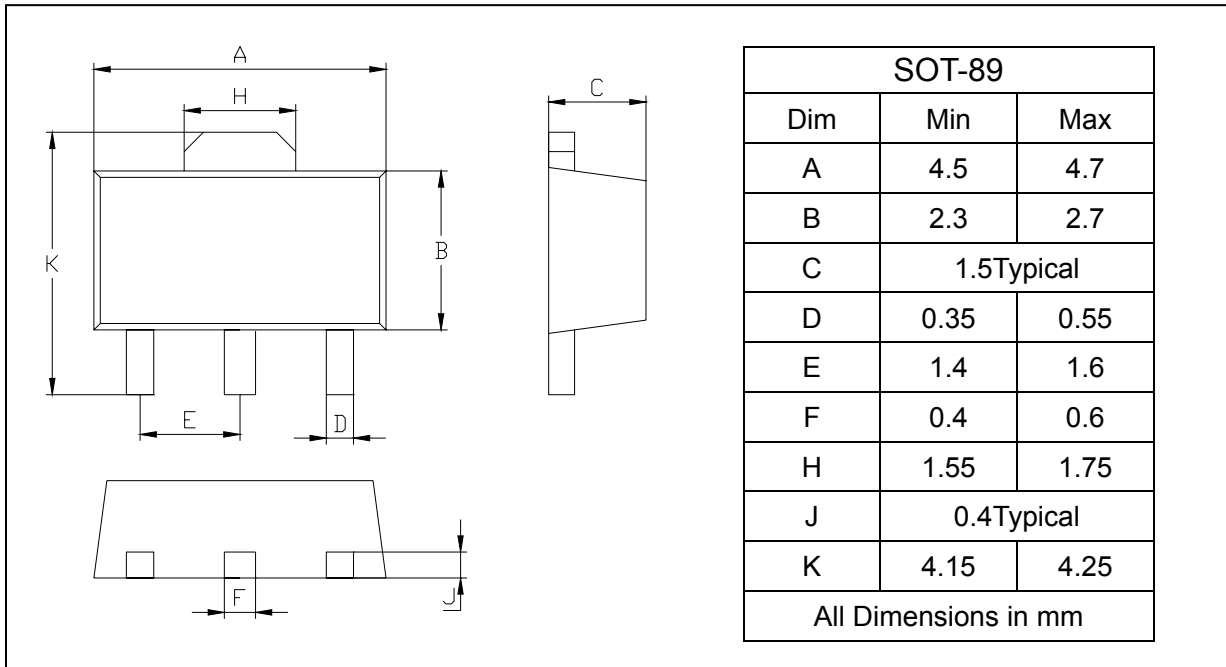
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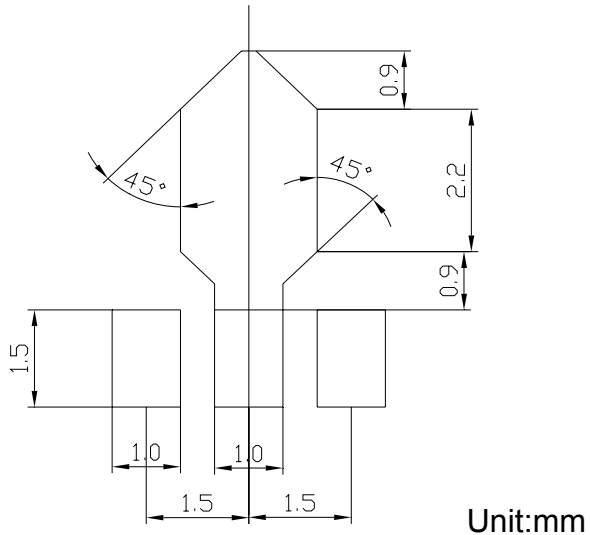
PACKAGE OUTLINE

Plastic surface mounted package

SOT-89



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
2SA1204	SOT-89	1000/Tape&Reel